SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE FOR CONNECTING SEMICONDUCTOR REGION AND ELECTRICAL WIRING METAL VIA TITANIUM SILICIDE LAYER AND METHOD OF FABRICATION THEREOF

A semiconductor device comprises a silicon substrate, an electrical wiring metal, an insulating film formed on the silicon substrate, a plurality of contact holes formed in the insulating film for connecting the silicon substrate and the electrical wiring metal to each other, and a titanium silicide film formed in the contact holes. The thickness of the titanium silicide film is 10 nm to 120 nm, or preferably, 20 nm to 84 nm. Semiconductor regions and the electrical wiring metal are connected to each other through the titanium silicide film.

(Figure 1)